















ESD

TVS

MOS

LDO

Diode

Sensor

DC-DC

Product Specification

Domestic Part Number	HER101 THRU HER108
Overseas Part Number	HER101 THRU HER108
▶ Equivalent Part Number	HER101 THRU HER108





HIGH EFFICIENCY RECTIFIER

REVERSE VOLTAGE: 50 to 1000 VOLTS FORWARD CURRENT: 1.0 AMPERE

FEATURES

 Plastic package has Underwriters Laboratory Flammability Classification 94V-O ctilizing Flame Retardant Epoxy Molding Compound.

- · Void-free Plastic in a DO-41 package.
- · Ultra Fast switching for high efficiency.
- · Exceeds environmental standards of MIL-S-19500/228

MECHANICAL DATA

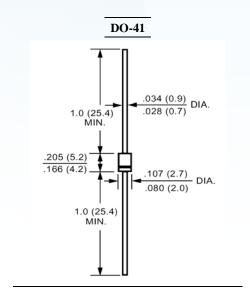
Case: Molded plastic, DO-41

Terminals: Axial leads, solderable per MIL-STD-202,

method 208 guaranteed

Polarity: Band denotes cathode

Mounting position: Any Weight: 0.013ounce, 0.3gram



Maximum Ratings and Electrical Characteristics

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

	Symbols	HER101	HER102	HER103	HER104	HER105	HER106	HER107	HER108	Units				
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	300	400	600	800	1000	Volts				
Maximum RMS Voltage	V _{RMS}	35	70	140	210	280	420	560	700	Volts				
Maximum DC Blocking Voltage	V _{DC}	50	100	200	300	400	600	800	1000	Volts				
Maximum Average Forward Rectified Current	т		10											
.375"(9.5mm) Lead Length at T _A =50℃	I _(AV)	1.0								Amp				
Peak Forward Surge Current,														
8.3ms single half-sine-wave	I_{FSM} 30								Amp					
superimposed on rated load (JEDEC method)														
Maximum Forward Voltage at 1.0A and T _A =25℃	$V_{\rm F}$		1.0		1	.3		1.7		Volts				
Maximum Reverse Current at T _J =25℃	T	5.0								uAmp				
at Rated DC Blocking Voltage T _J =100℃	I_R	50												
Typical Junction Capacitance (Note 1)	$C_{\mathbf{J}}$	17								рF				
Maximum Reverse Recovery Time (Note 2)	T_{RR}	50 75							nS					
Typical Thermal Resistance (Note 3)	$R_{\theta JA}$	60							°C/W					
Operating and Storage Temperature Range	T _J , Tstg	-55 to +150								င				

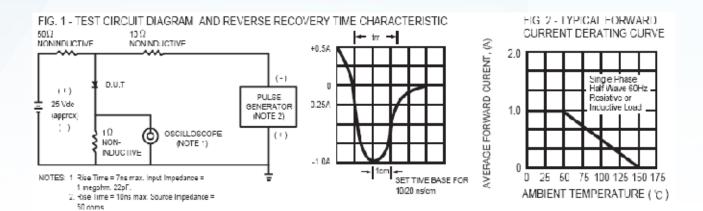
NOTES:

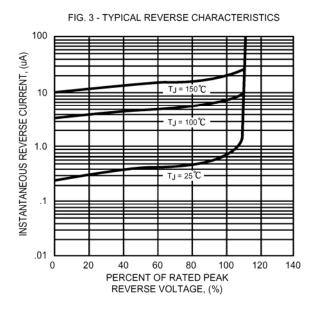
- 1- Measured at 1 MHz and applied reverse voltage of 4.0 VDC.
- 2- Reverse Recovery Test Conditions: I_F =.5A, I_R =1A, I_{RR} =.25A.
- 3- Thermal Resistance from Junction to Ambient at 0.375"(9.5mm) lead length P.C.B. Mounted.

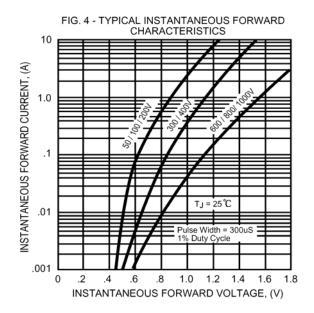


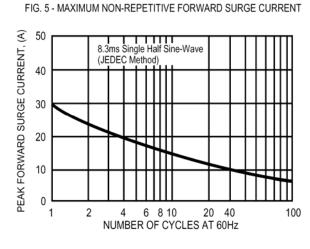
HIGH EFFICIENCY RECTIFIER

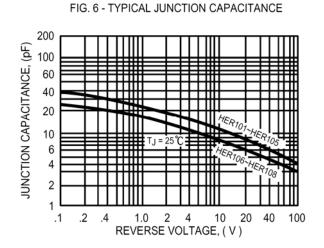
RATINGS AND CHARACTERISTIC CURVES













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